Code No: 152AE  JAWAHARLAL NEHRU TECHNOLOGICAL UNIVERSITY HYDERABAD  B.Tech I Year II Semester Examinations, May - 2019  APPLIED PHYSICS  (Common to EEE, CSE, IT)								
3 K	Time: 3 hours (Common to EEE, CSE, II)  Max. Marks: 7	5						
	Note: This question paper contains two parts A and B.  Part A is compulsory which carries 25 marks. Answer all questions in Part A  Part B consists of 5 Units. Answer any one full question from each unit. Each question  carries 10 marks and may have a, b, c as sub questions.	٩. n						
3 R	SP SPART-ASH SH (25 Marks	3)						
3R	1.a) What is Photo-electric effect. Give the Einstein's equation.  b) What are donors and acceptors? Give two examples of each.  c) What are direct and Indirect band gap semiconductors  d) Explain Population Inversion and how is it achieved?  e) State the Faraday's Law.  f) Give the Born's interpretation of wave function.  [3]  g) Explain the concept of Hall effect.  h) Give three differences between semiconductor laser and LED.  i) Explain the construction of optical fiber.  j) Derive the relation between \$\bar{B}\$, \$\bar{H}\$ and \$\bar{M}\$  [3]							
38	SR SR SPART-B SR (50 Marks)	s)						
	<ul> <li>2.a) Derive an expression for the wavelength λ of the matter waves.</li> <li>b) Describe a experiment to verify the existence of matter waves.</li> <li>c) For an electron in a one-dimensional infinite potential well of width 1A<sup>0</sup>, calculate the energy separation between the two lowest energy levels and also calculate the frequency of the energy separation between the two lowest energy levels.</li> </ul>	ne Ly						

and wavelength of the photon corresponding to a train [10]

Explain Heisenberg's Uncertainty principle. 3.a)

Using the Heisenberg's Uncertainty principle explain why electron cannot exist in the b) nucleus of radius 10<sup>-14</sup>m.

Show that the particle trapped in a potential box possesses discrete energy levels. [10] c)

What are intrinsic and extrinsic semiconductors? 4.a)

Distinguish between N-type and P-type semiconductors with an example. b)

A rectangular plate of a semiconductor has dimensions 2.0 cm along y direction, 1.0 mm c) along z-direction. Hall probes are attached on its two surfaces parallel to x z plane and a magnetic field of 1.0 tesla is applied along z-direction. A current of 3.0 mA is set up along the x direction. Calculate the hall voltage measured by the probes, if the hall coefficient of the material is 3.66 × 10<sup>-4</sup> m<sup>3</sup>/C. Also, calculate the charge carrier [10].. concentration.

8R	(	3R 8R (	38	SR.		8R			
	5.a) b)	The conductivity of N-type G electrons in Germanium is 0.39 Define Fermi level. Where do semiconductor and N- type sen	9 m <sup>2</sup> V <sup>-1</sup> s <sup>-1</sup> , then es a Fermi leve niconductor at r	find the concent le exist in a Intrangement	tration of the do insic semicondurature?	nor atoms. ctor, P-type			
3H	c)	Explain the working for a Com	mon Base PNP	transistor with	a suitable circuit	diagram. [10]			
	6.a) b)	What is a photodetector? Explay When $3 \times 10^{11}$ photons each waverage $1.2 \times 10^{11}$ electrons responsivity.	ith wavelength	of 0.85µm are i	ncident on a pho	todiode, on			
3R	c) (	What is a solar cell? Explain w	ith a neat diagra  OR	am. Define the e	fficiency and fil	l factor. [10]			
	7.a)	Explain the construction and we	orking of a LEI	Э.					
	b)	What are the major differences	between PIN ar	nd Avalanche pl	notodiode?				
	c)	A silicon photodiode has quant		of 65% with ph	oton energy 1.5	×10 <sup>-19</sup> J. Its			
		band gap energy is 0.67eV. Cal	culate:						
		i) Responsivity (R)		() []		CHI			
	(	ii) Incident power required to o	otain a photo cu	irrent 2.5 μA (P	o)?:	[10]			
	8.a)	Explain the construction, princi	ple and working	of Ruby laser.					
	b)	A He-Ne gas laser of wavelengt				How many			
		photons are emitted each minute			0. 0. 2.3 mm.	now many			
	c)	Explain about the different mo			gh step-index a	nd graded-			
	r pour	index fiber?	0.5			[10]			
5   <	9.a)	Flahorate the various application	OR	> (	ing and military				
5.00	<ul><li>9.a) Elaborate the various applications of laser in the field of medicine and military.</li><li>b) Discuss the concept of Acceptance angle and Acceptance cone of a fiber. Derive a</li></ul>								
	0)	relation between acceptance a materials.	ngle and the	refractive indic	ces of core and	d cladding			
	c)	The numerical aperture of an o							
9 m		refractive index of cladding; ii per unit refractive index of the c	ore.	change in core	cladding refrac	tive index			
		ik ok (	)						
	10.a)	What is dielectric polarization?							
	b)	Derive Clausius-Mosotti relation			•	[10]			
	c)	Write notes on ferroelectricity and	ia piezoeiectric	ity.		[10]			
	11.a)	Derive a relation between electr		and electric sus	ceptibility of the	dielectric			
	7	medium.	virs i						
	b)	Describe dielectric displacement	, dielectric loss,	dielectric stren	gth.				
	c)	Describe the Hysteresis loop of hard and soft magnetic materials	ferromagnets. F			h between [10]			
						-			
			00O00						
-/	, marine	Annual Sand Inner San	00000	ency persons	green, warm				
3 H		R 8R E	ßR {	3H	8R -	8R			